WHAT IS CLAIMED IS:

1. A thermoelectric semiconductor element, comprising:

a first section; and

a second section, wherein a cross-section of the first section is greater than a cross-section of the second section.

2. The thermoelectric semiconductor element according to claim 1, wherein the first section is adjacent to a hot side of the thermoelectric semiconductor element.

3. The thermoelectric semiconductor element according to claim 1, wherein the second section is adjacent to a cold side of the thermoelectric semiconductor element.

4. The thermoelectric semiconductor element according to claim 1, wherein the first section is closer to a hot side of the thermoelectric semiconductor element than the second section.

5. The thermoelectric semiconductor element according to claim 1, wherein the thermoelectric semiconductor element is asymmetrical.

6. A semiconductor thermoelectric module, comprising:

a plurality of semiconductor elements each having a first section and a second section, wherein a cross-section of the first section is greater than a cross-section of the second section.

7. The semiconductor thermoelectric module according to claim 6, wherein the first section is adjacent to a hot side of the semiconductor thermoelectric module.

8. The semiconductor thermoelectric module according to claim 6, wherein the second section is adjacent to a cold side of the semiconductor thermoelectric module.

9. The semiconductor thermoelectric module according to claim 6, wherein the first section is closer to a hot side of the semiconductor thermoelectric module than the second section.

10. The semiconductor thermoelectric module according to claim 6, wherein the semiconductor elements are asymmetrical.

11. A semiconductor thermoelectric generator, comprising:

a plurality of thermoelectric modules each having a plurality of semiconductor elements connected electrically in series via electrical conductors to a first side of the thermoelectric modules and to a second side of the thermoelectric modules, wherein each of the plurality of semiconductor elements has a first section and a second section, and a cross-section of the first section is greater than a cross-section of the second section.

12. The semiconductor thermoelectric generator according to claim 11, wherein the first section is adjacent to a hot side of the semiconductor thermoelectric modules.

13. The semiconductor thermoelectric generator according to claim 11, wherein the second section is adjacent to a cold side of the semiconductor thermoelectric modules.

14. The semiconductor thermoelectric generator according to claim 11, wherein the first section is closer to a hot side of the semiconductor thermoelectric modules than the second section.

15. The semiconductor thermoelectric generator according to claim 11, wherein the semiconductor elements are asymmetrical.

16. A thermoelectric semiconductor element, comprising:

a first section; and

a second section, wherein a heat path of the first section is greater than a heat path of the second section.

17. The thermoelectric semiconductor element according to claim 16, wherein the first section is adjacent to a hot side of the thermoelectric semiconductor element.

18. The thermoelectric semiconductor element according to claim 16, wherein the second section is adjacent to a cold side of the thermoelectric semiconductor element.

19. The thermoelectric semiconductor element according to claim 16, wherein the first section is closer to a hot side of the thermoelectric semiconductor element than the second section.

20. The thermoelectric semiconductor element according to claim 16, wherein the thermoelectric semiconductor element is asymmetrical.